
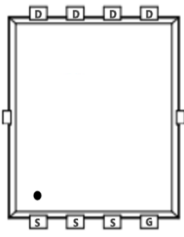
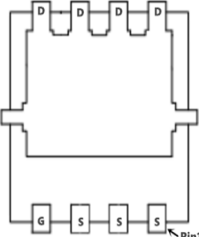
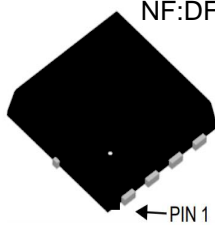
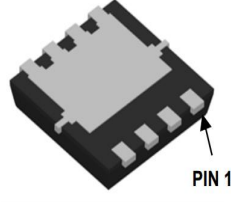
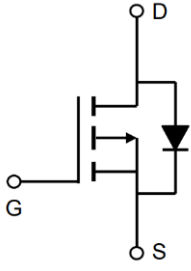




# TM50P03NF

## P-Channel Enhancement Mosfet

<p><b>General Description</b></p> <ul style="list-style-type: none"> <li>• Low <math>R_{DS(ON)}</math></li> <li>• RoHS and Halogen-Free Compliant</li> </ul> <p><b>Applications</b></p> <ul style="list-style-type: none"> <li>• Load switch</li> <li>• PWM</li> </ul>	<p><b>General Features</b></p> <p><math>V_{DS} = -30V</math> <math>I_D = -50A</math></p> <p><math>R_{DS(ON)} = 8.7m\Omega</math>(typ.) @ <math>V_{GS} = -10V</math></p> <p>100% UIS Tested              100% <math>R_g</math> Tested</p> <div style="text-align: right;">  </div>
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Marking: 50P03

**Absolute Maximum Ratings** ( $T_A = 25^\circ C$  Unless Otherwise Noted)

Symbol	Parameter	Rating		Units
		10s	Steady State	
$V_{DS}$	Drain-Source Voltage	-30		V
$V_{GS}$	Gate-Source Voltage	$\pm 25$		V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-50		A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-32		A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	-150		A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	125		mJ
$I_{AS}$	Avalanche Current	-50		A
$P_D @ T_A = 25^\circ C$	Total Power Dissipation <sup>4</sup>	5	2.0	W
$T_{STG}$	Storage Temperature Range	-55 to 150		$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150		$^\circ C$

**Thermal Data**

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient <sup>1</sup>	---	62	$^\circ C/W$



**TM50P03NF**

**P-Channel Enhancement Mosfet**

**Electrical Characteristics** ( $T_J=25^{\circ}\text{C}$  unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
<b>Off Characteristic</b>						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-30	-	-	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=-30V, V_{GS}=0V,$	-	-	-1	$\mu A$
$I_{GSS}$	Gate to Body Leakage Current	$V_{DS}=0V, V_{GS}=\pm 20V$	-	-	$\pm 100$	nA
<b>On Characteristics</b>						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1.0	-1.5	-2.5	V
$R_{DS(on)}$	Static Drain-Source on-Resistance <small>Note3</small>	$V_{GS}=-10V, I_D=-10A$	-	8.7	14	m $\Omega$
		$V_{GS}=-4.5V, I_D=-5A$	-	17	24	
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{DS}=-15V, V_{GS}=0V,$ $f=1.0MHz$	-	1770	-	pF
$C_{oss}$	Output Capacitance		-	233	-	pF
$C_{rss}$	Reverse Transfer Capacitance		-	206	-	pF
$Q_g$	Total Gate Charge	$V_{DS}=-15V, I_D=-5A,$ $V_{GS}=-10V$	-	22	-	nC
$Q_{gs}$	Gate-Source Charge		-	1.0	-	nC
$Q_{gd}$	Gate-Drain("Miller") Charge		-	1.8	-	nC
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-on Delay Time	$V_{DD}=-15V, I_D=-10A,$ $V_{GS}=-10V, R_{GEN}=2.5\Omega$	-	9	-	ns
$t_r$	Turn-on Rise Time		-	13	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	48	-	ns
$t_f$	Turn-off Fall Time		-	20	-	ns
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
$I_S$	Maximum Continuous Drain to Source Diode Forward Current		-	-	-50	A
$I_{SM}$	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-60	A
$V_{SD}$	Drain to Source Diode Forward Voltage	$V_{GS}=0V, I_S=-15A$	-	-0.8	-1.2	V
$t_{rr}$	Reverse Recovery Time	$T_J=25^{\circ}\text{C},$	-	64	-	ns
$Q_{rr}$	Reverse Recovery Charge	$V_{DD}=-24V, I_F=-2.8A,$ $di/dt=-100A/\mu s$	-	25	-	nC

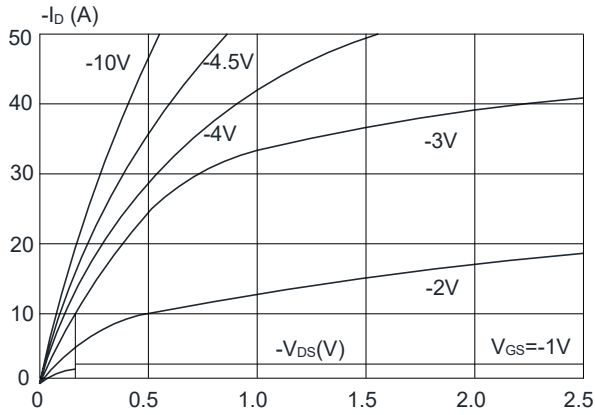
Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition:  $T_J=25^{\circ}\text{C}, V_{GS}=10V, R_G=25\Omega, L=0.5mH, I_{AS}=-12.7A$

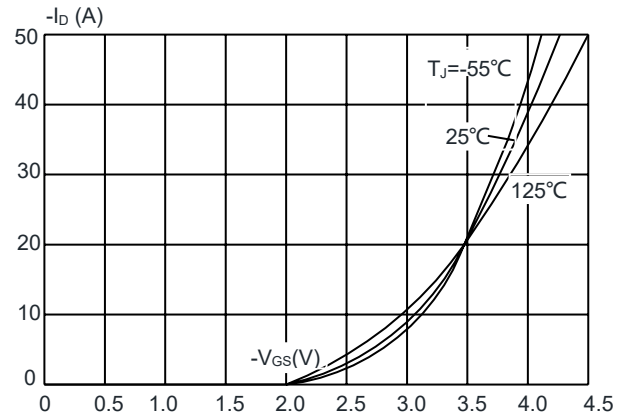
3. Pulse Test: Pulse Width $\leq 300\mu s$ , Duty Cycle $\leq 0.5\%$

## Typical Performance Characteristics

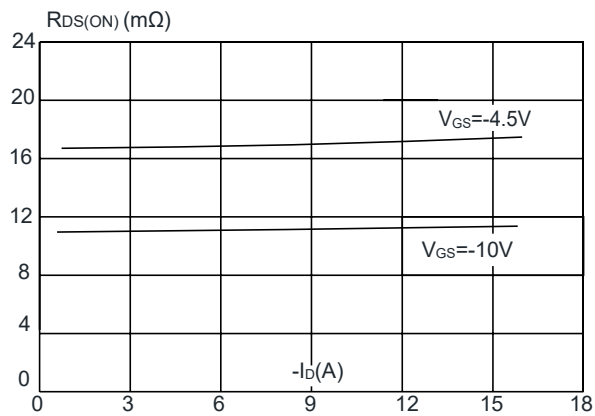
**Figure 1: Output Characteristics**



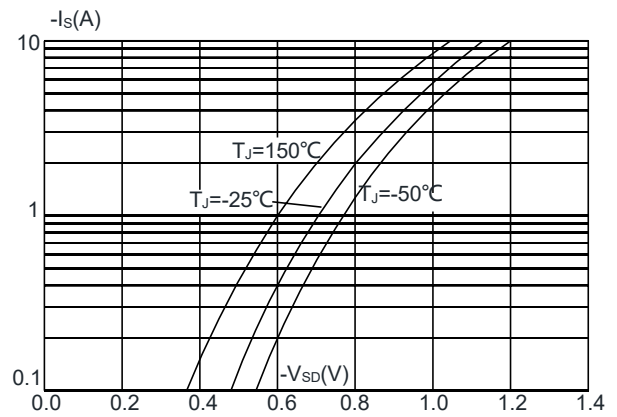
**Figure 2: Typical Transfer Characteristics**



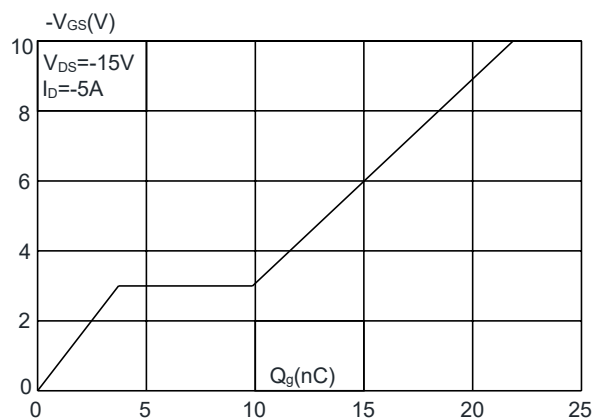
**Figure 3: On-resistance vs. Drain Current**



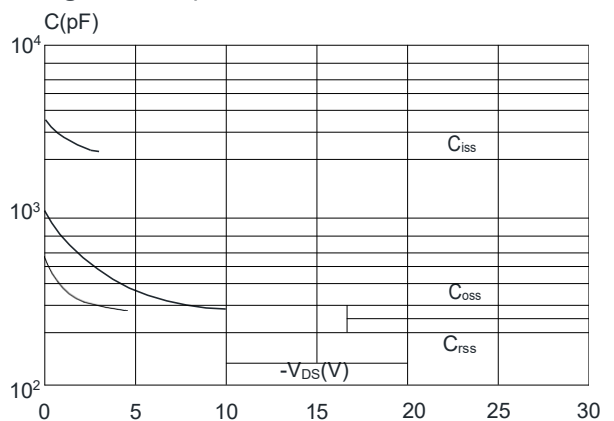
**Figure 4: Body Diode Characteristics**



**Figure 5: Gate Charge Characteristics**



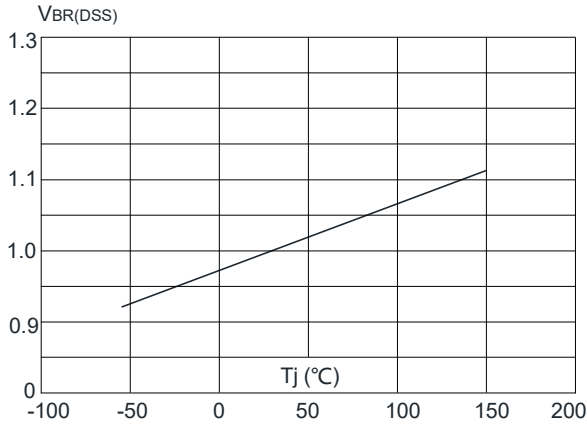
**Figure 6: Capacitance Characteristics**



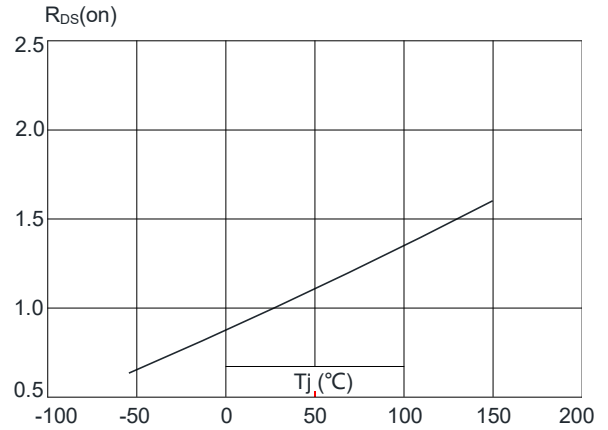
**TM50P03NF**

**P-Channel Enhancement Mosfet**

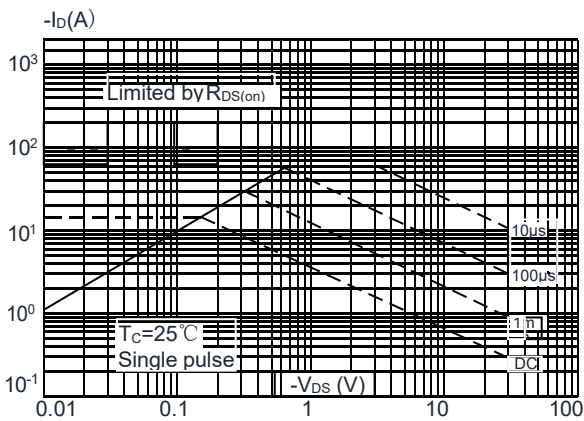
**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature



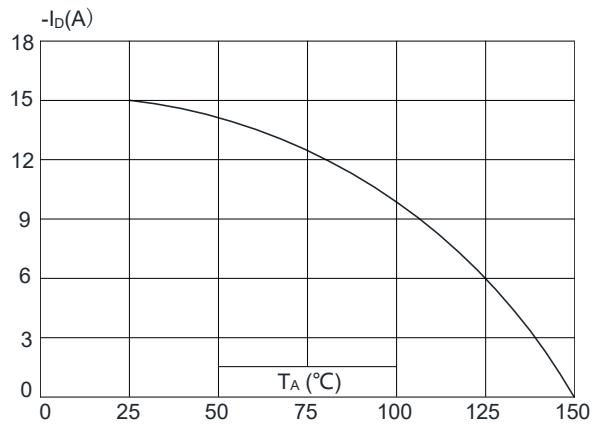
**Figure 8:** Normalized on Resistance vs. Junction Temperature



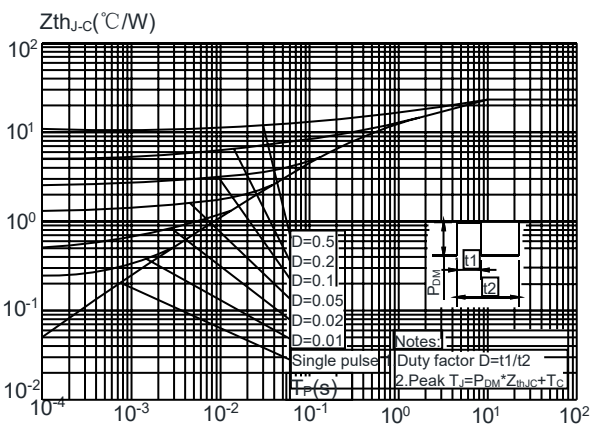
**Figure 9:** Maximum Safe Operating Area



**Figure 10:** Maximum Continuous Drain Current vs. Ambient Temperature



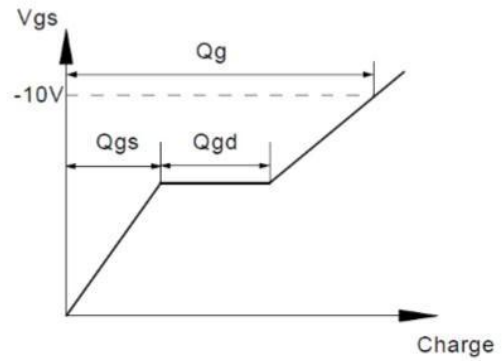
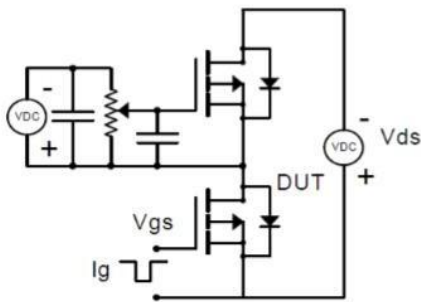
**Figure.11:** Maximum Effective Transient Thermal Impedance, Junction-to-Case



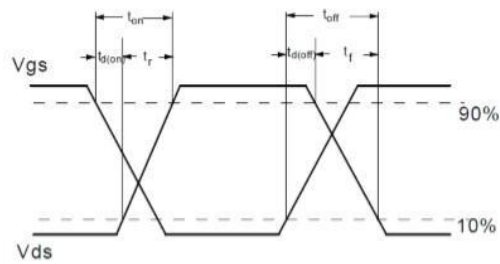
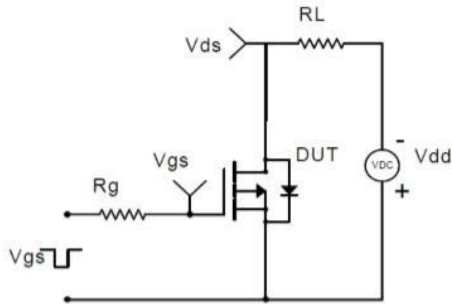


Test Circuit

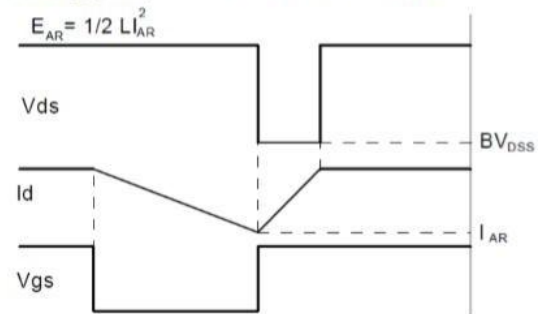
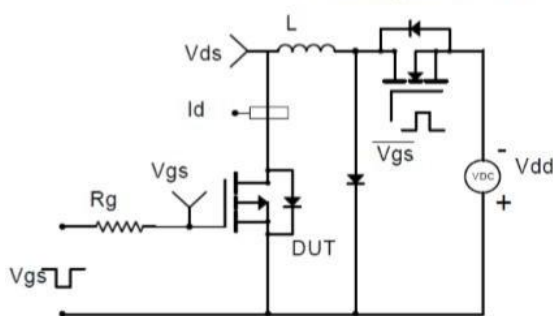
Gate Charge Test Circuit & Waveform



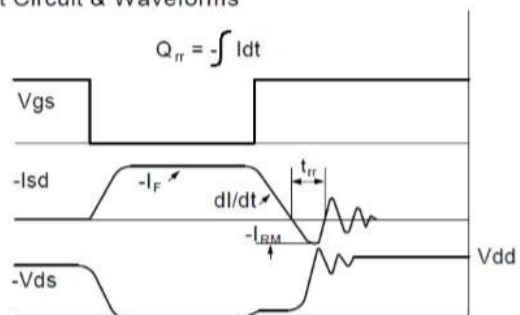
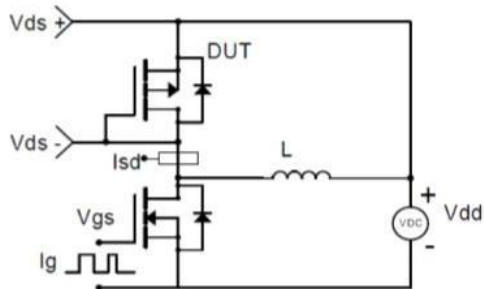
Resistive Switching Test Circuit & Waveforms



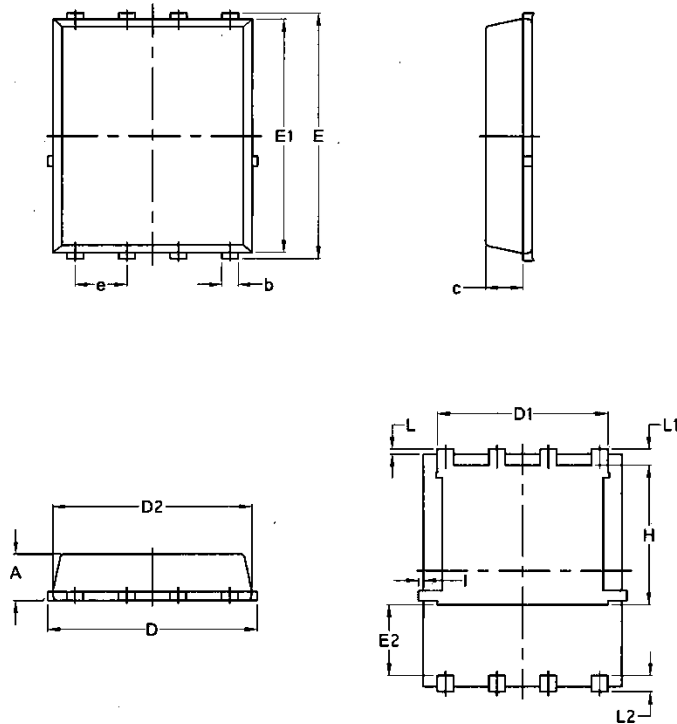
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



# Package Mechanical Data: DFN5x6-8L



Symbol	Common			
	mm		Inch	
	Min	Max	Min	Max
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.0970	0.0324	0.082
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.95	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	/	0.0630	/
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	/	0.18	/	0.0070